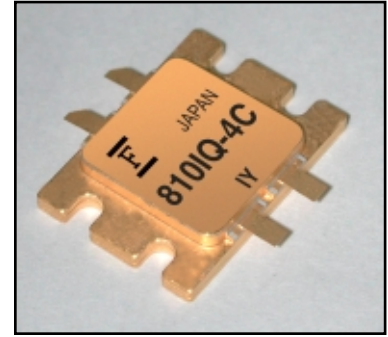


# FLL810IQ-4C

## L-Band High Power GaAs FET

### FEATURES

- Push-Pull Configuration
- High Power Output: 80W
- High PAE: 45%.
- Excellent Linearity
- Suitable for class AB operation.
- Hermetically Sealed Package



### DESCRIPTION

The FLL810IQ-4C is an 80 Watt GaAs FET that employs a push-pull design which offers excellent linearity, ease of matching, and greater consistency in covering the frequency band of 3.5 to 3.7 GHz. This new product is uniquely suited for use in WLL applications as it offers high gain, long term reliability and ease of use.

### ABSOLUTE MAXIMUM RATINGS (Ambient Temperature $T_a=25^{\circ}\text{C}$ )

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	$V_{DS}$		15	V
Gate-Source Voltage	$V_{GS}$		-5	V
Total Power Dissipation	$P_T$	$T_c = 25^{\circ}\text{C}$	136	W
Storage Temperature	$T_{stg}$		-65 to +175	$^{\circ}\text{C}$
Channel Temperature	$T_{ch}$		+175	$^{\circ}\text{C}$

Fujitsu recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage ( $V_{DS}$ ) should not exceed 12 volts.
2. The forward and reverse gate currents should not exceed 176 and -51.8 mA respectively with gate resistance of  $5\Omega$ .
3. The operating channel temperature ( $T_{ch}$ ) should not exceed  $145^{\circ}\text{C}$ .

### ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25^{\circ}\text{C}$ )

Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Drain Current	$I_{DSS}$	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	-	8	-	A
Pinch-Off Voltage	$V_p$	$V_{DS} = 5\text{V}, I_{DS} = 220\text{mA}$	-0.1	-0.3	-0.5	V
Gate-Source Breakdown Voltage	$V_{GSO}$	$I_{GS} = -2.2\text{mA}$	-5	-	-	V
Output Power	$P_{out}$	$V_{DS} = 12\text{V}$ $f = 3.6\text{GHz}$ $I_{DS} = 5.0\text{A}$ $P_{in} = 43.0\text{dBm}$	48.0	49.0	-	dBm
Linear Gain (Note 1)	GL		8.5	9.5	-	dB
Power-Added Efficiency	$\eta_{add}$		-	45	-	%
Drain Current	$I_{DSR}$		-	11.5	15.0	A
Thermal Resistance	$R_{th}$	Channel to Case	-	0.8	1.1	$^{\circ}\text{C}/\text{W}$

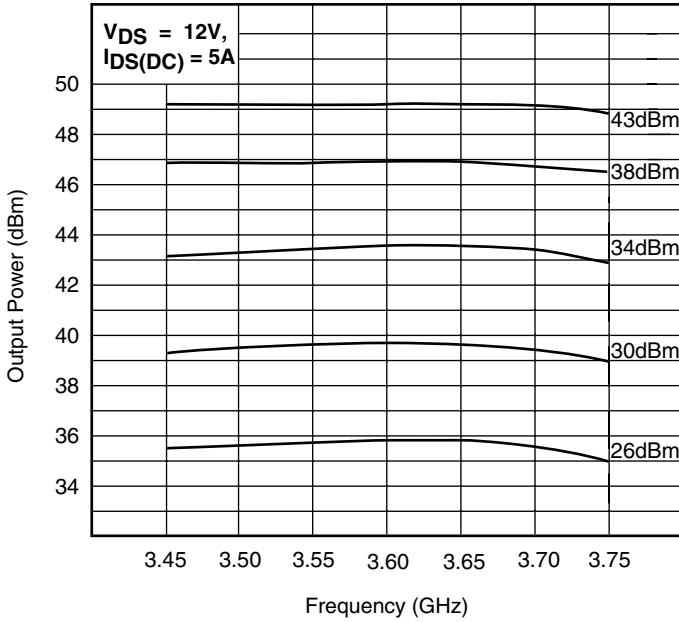
### CASE STYLE: IQ

Note 1: The condition for GL is the same as  $P_{out}$  except  $P_{in} = 28.0\text{dBm}$ .

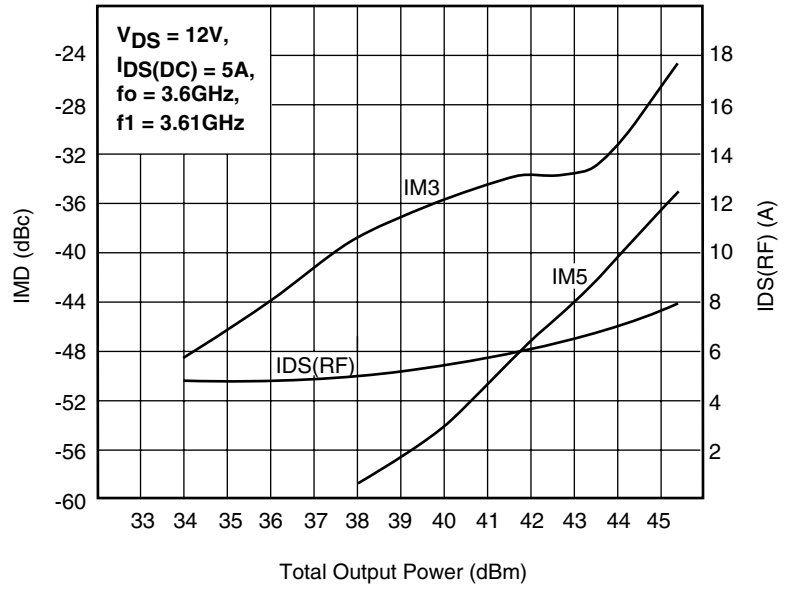
# FLL810IQ-4C

## L-Band High Power GaAs FET

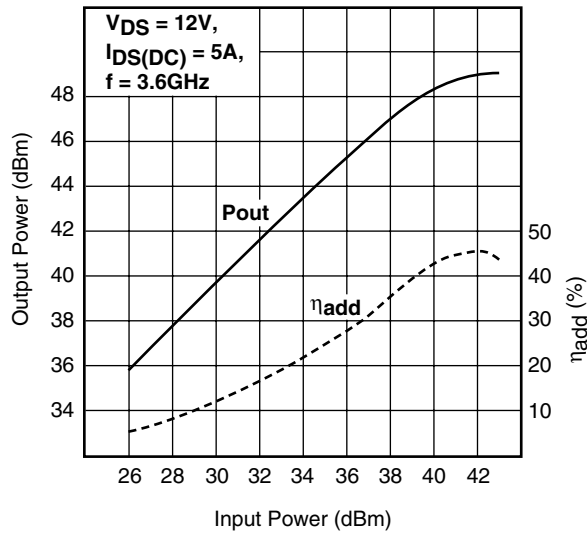
OUTPUT POWER vs. FREQUENCY



IMD & IDS(RF) vs. TOTAL OUTPUT POWER



OUTPUT POWER &  $\eta_{add}$  vs. INPUT POWER



# FLL810IQ-4C

## L-Band High Power GaAs FET

### S-PARAMETERS

$V_{DS} = 12V, I_{DS} = 2500mA$

FREQUENCY (MHZ)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
2500	.499	-103.9	1.973	-113.4	.017	-111.7	.796	152.9
2600	.617	-120.1	1.880	-125.9	.017	-134.2	.773	151.8
2700	.703	-131.7	1.735	-142.2	.016	-149.9	.752	150.1
2800	.761	-141.4	1.784	-153.8	.016	-167.5	.729	149.5
2900	.793	-148.6	1.689	-163.9	.017	-176.4	.714	148.0
3000	.801	-155.5	1.803	-178.8	.017	161.0	.678	146.2
3100	.783	-162.8	1.949	171.0	.019	136.6	.656	143.9
3200	.747	-169.1	2.087	154.5	.021	119.4	.604	140.8
3300	.644	-176.8	2.398	136.9	.024	94.7	.566	138.8
3400	.492	178.6	2.627	116.1	.031	80.3	.506	137.6
3500	.315	-166.2	2.798	88.0	.036	48.3	.468	143.3
3600	.397	-130.1	2.612	59.6	.034	15.7	.504	148.1
3700	.603	-128.8	2.173	33.1	.031	-8.8	.558	145.3
3800	.743	-135.6	1.814	13.3	.024	-33.0	.580	136.4
3900	.825	-143.0	1.493	-5.2	.022	-47.8	.559	125.9
4000	.878	-148.0	1.222	-20.4	.019	-59.2	.535	113.4
4100	.910	-152.6	.999	-34.6	.019	-67.0	.483	97.7
4200	.937	-156.1	.849	-46.9	.017	-76.4	.418	78.8
4300	.949	-159.8	.735	-55.8	.018	-86.6	.376	53.9
4400	.953	-162.7	.681	-67.5	.018	-96.7	.343	18.9
4500	.956	-165.1	.666	-82.1	.020	-107.9	.386	-17.4

Note: This S-Parameter data shows measurements performed on a single-ended push-pull FET. These parameters should be used to determine the calculated Push-Pull S-Parameter amplifier designs.

